

# MC74HC04A

## Hex Inverter

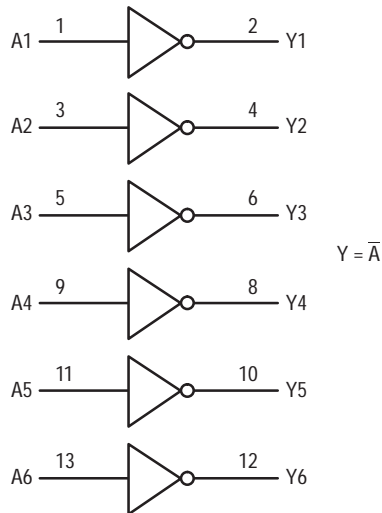
### High-Performance Silicon-Gate CMOS

The MC74HC04A is identical in pinout to the LS04 and the MC14069. The device inputs are compatible with Standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

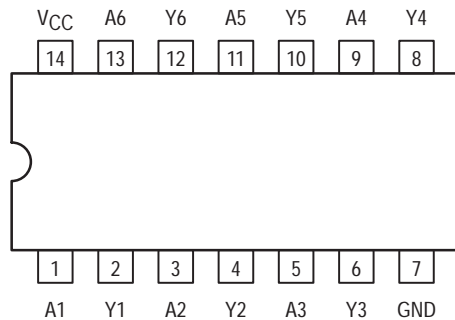
The device consists of six three-stage inverters.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2 to 6V
- Low Input Current: 1µA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 36 FETs or 9 Equivalent Gates

#### LOGIC DIAGRAM



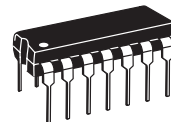
#### Pinout: 14-Lead Packages (Top View)



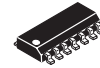
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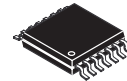
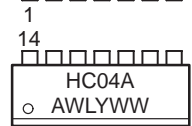
#### MARKING DIAGRAMS



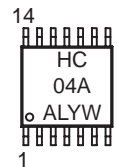
**PDIP-14**  
N SUFFIX  
CASE 646



**SOIC-14**  
D SUFFIX  
CASE 751A



**TSSOP-14**  
DT SUFFIX  
CASE 948G



A = Assembly Location  
WL or L = Wafer Lot  
YY or Y = Year  
WW or W = Work Week

#### FUNCTION TABLE

Inputs	Outputs
A	Y
L	H
H	L

#### ORDERING INFORMATION

Device	Package	Shipping
MC74HC04AN	PDIP-14	2000 / Box
MC74HC04AD	SOIC-14	55 / Rail
MC74HC04ADR2	SOIC-14	2500 / Reel
MC74HC04ADT	TSSOP-14	96 / Rail
MC74HC04ADTR2	TSSOP-14	2500 / Reel

# MC74HC04A

## MAXIMUM RATINGS\*

Symbol	Parameter	Value	Unit
$V_{CC}$	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
$V_{in}$	DC Input Voltage (Referenced to GND)	- 0.5 to $V_{CC} + 0.5$	V
$V_{out}$	DC Output Voltage (Referenced to GND)	- 0.5 to $V_{CC} + 0.5$	V
$I_{in}$	DC Input Current, per Pin	$\pm 20$	mA
$I_{out}$	DC Output Current, per Pin	$\pm 25$	mA
$I_{CC}$	DC Supply Current, $V_{CC}$ and GND Pins	$\pm 50$	mA
PD	Power Dissipation in Still Air, Plastic DIP†	750	mW
	SOIC Package†	500	
	TSSOP Package†	450	
$T_{stg}$	Storage Temperature	- 65 to + 150	°C
$T_L$	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP, SOIC or TSSOP Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation,  $V_{in}$  and  $V_{out}$  should be constrained to the range  $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$ . Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or  $V_{CC}$ ). Unused outputs must be left open.

\*Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

†Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C  
SOIC Package: - 7 mW/°C from 65° to 125°C  
TSSOP Package: - 6.1 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
$V_{CC}$	DC Supply Voltage (Referenced to GND)	2.0	6.0	V	
$V_{in}, V_{out}$	DC Input Voltage, Output Voltage (Referenced to GND)	0	$V_{CC}$	V	
$T_A$	Operating Temperature, All Package Types	- 55	+ 125	°C	
$t_r, t_f$	Input Rise and Fall Time (Figure 1)	$V_{CC} = 2.0 \text{ V}$	0	1000	ns
		$V_{CC} = 4.5 \text{ V}$	0	500	
		$V_{CC} = 6.0 \text{ V}$	0	400	

# MC74HC04A

## DC CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Condition	V <sub>CC</sub> V	Guaranteed Limit			Unit
				-55 to 25°C	≤85°C	≤125°C	
V <sub>IH</sub>	Minimum High-Level Input Voltage	V <sub>out</sub> = 0.1V or V <sub>CC</sub> - 0.1V  I <sub>out</sub>   ≤ 20μA	2.0	1.50	1.50	1.50	V
			3.0	2.10	2.10	2.10	
			4.5	3.15	3.15	3.15	
			6.0	4.20	4.20	4.20	
V <sub>IL</sub>	Maximum Low-Level Input Voltage	V <sub>out</sub> = 0.1V or V <sub>CC</sub> - 0.1V  I <sub>out</sub>   ≤ 20μA	2.0	0.50	0.50	0.50	V
			3.0	0.90	0.90	0.90	
			4.5	1.35	1.35	1.35	
			6.0	1.80	1.80	1.80	
V <sub>OH</sub>	Minimum High-Level Output Voltage	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 20μA	2.0	1.9	1.9	1.9	V
			4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
		V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 2.4mA  I <sub>out</sub>   ≤ 4.0mA  I <sub>out</sub>   ≤ 5.2mA	3.0	2.48	2.34	2.20	
			4.5	3.98	3.84	3.70	
			6.0	5.48	5.34	5.20	
V <sub>OL</sub>	Maximum Low-Level Output Voltage	V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 20μA	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
		V <sub>in</sub> = V <sub>IH</sub> or V <sub>IL</sub>  I <sub>out</sub>   ≤ 2.4mA  I <sub>out</sub>   ≤ 4.0mA  I <sub>out</sub>   ≤ 5.2mA	3.0	0.26	0.33	0.40	
			4.5	0.26	0.33	0.40	
			6.0	0.26	0.33	0.40	
I <sub>in</sub>	Maximum Input Leakage Current	V <sub>in</sub> = V <sub>CC</sub> or GND	6.0	± 0.1	± 1.0	± 1.0	μA
I <sub>CC</sub>	Maximum Quiescent Supply Current (per Package)	V <sub>in</sub> = V <sub>CC</sub> or GND I <sub>out</sub> = 0μA	6.0	1.0	10	40	μA

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

## AC CHARACTERISTICS (C<sub>L</sub> = 50pF, Input t<sub>r</sub> = t<sub>f</sub> = 6ns)

Symbol	Parameter	V <sub>CC</sub> V	Guaranteed Limit			Unit
			-55 to 25°C	≤85°C	≤125°C	
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, Input A or B to Output Y (Figures 1 and 2)	2.0	75	95	110	ns
		3.0	30	40	55	
		4.5	15	19	22	
		6.0	13	16	19	
t <sub>TLH</sub> , t <sub>THL</sub>	Maximum Output Transition Time, Any Output (Figures 1 and 2)	2.0	75	95	110	ns
		3.0	27	32	36	
		4.5	15	19	22	
		6.0	13	16	19	
C <sub>in</sub>	Maximum Input Capacitance		10	10	10	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

C <sub>PD</sub>	Power Dissipation Capacitance (Per Inverter)*	Typical @ 25°C, V <sub>CC</sub> = 5.0 V		pF
		20		

\* Used to determine the no-load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> V<sub>CC</sub><sup>2</sup>f + I<sub>CC</sub> V<sub>CC</sub>. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

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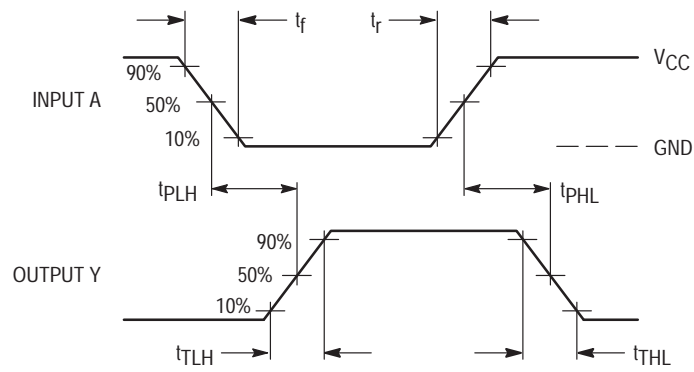
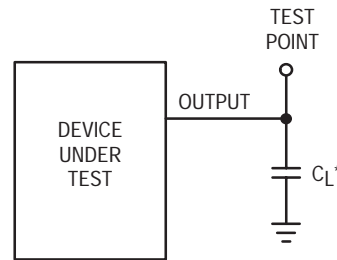


Figure 1. Switching Waveforms



\*Includes all probe and jig capacitance

Figure 2. Test Circuit

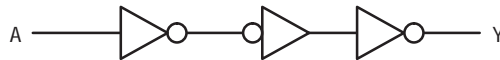
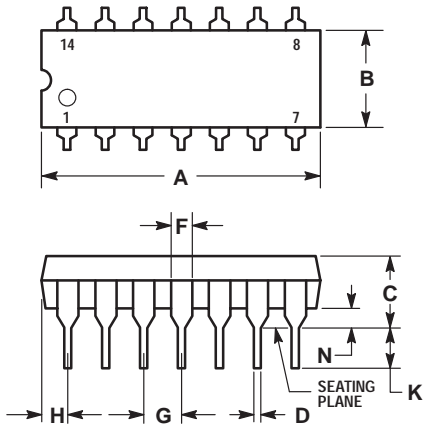


Figure 3. Expanded Logic Diagram  
(1/6 of the Device Shown)

# MC74HC04A

## PACKAGE DIMENSIONS

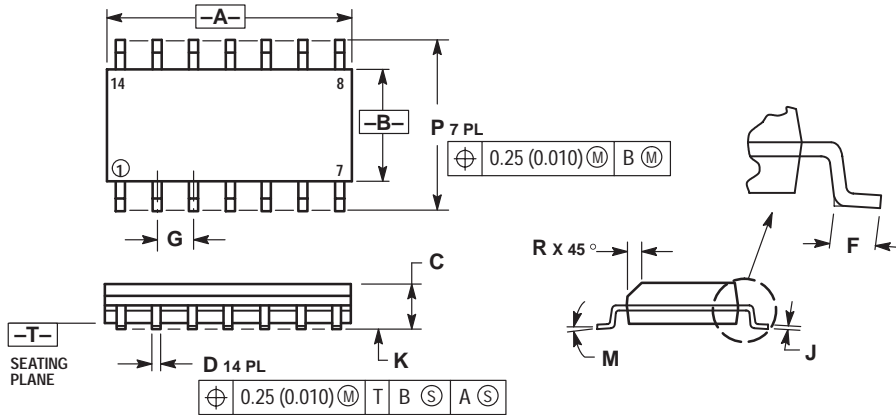
**PDIP-14  
N SUFFIX  
CASE 646-06  
ISSUE L**



- NOTES:
- LEADS WITHIN 0.13 (0.005) RADIUS OF TRUE POSITION AT SEATING PLANE AT MAXIMUM MATERIAL CONDITION.
  - DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
  - DIMENSION B DOES NOT INCLUDE MOLD FLASH.
  - ROUNDED CORNERS OPTIONAL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.715	0.770	18.16	19.56
B	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
H	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.300 BSC		7.62 BSC	
M	0°	10°	0°	10°
N	0.015	0.039	0.39	1.01

**SOIC-14  
D SUFFIX  
CASE 751A-03  
ISSUE F**



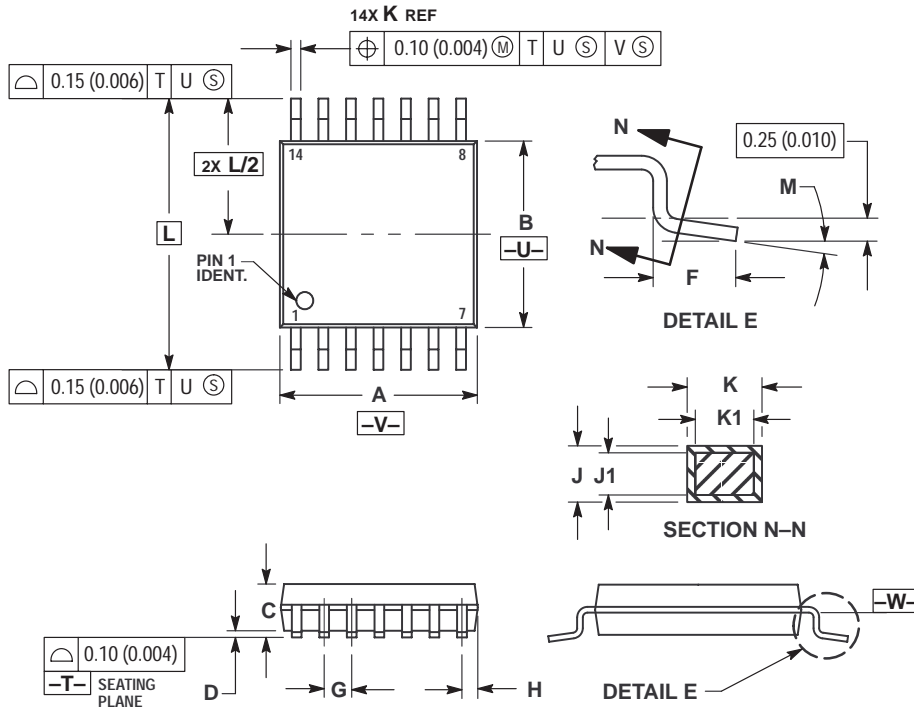
- NOTES:
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  - CONTROLLING DIMENSION: MILLIMETER.
  - DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
  - MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
  - DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

# MC74HC04A

## PACKAGE DIMENSIONS

TSSOP-14  
DT SUFFIX  
CASE 948G-01  
ISSUE O



### NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -V-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

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